

Silicon PNP Power Transistors

2SB1436

DESCRIPTION

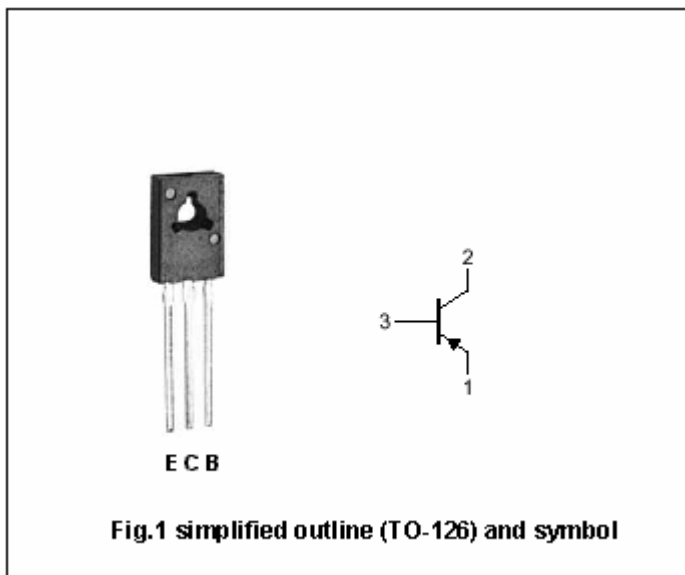
- With TO-126 package
- Complement to type 2SD2166
- Low collector saturation voltage

APPLICATIONS

- For audio power amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-30	V
V _{CEO}	Collector-emitter voltage	Open base	-20	V
V _{EBO}	Emitter-base voltage	Open collector	-6	V
I _C	Collector current (DC)		-5	A
I _{CM}	Collector current-Peak		-10	A
P _D	Total power dissipation	T _a =25°C	1.5	W
		T _C =25°C	5	
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

Silicon PNP Power Transistors

2SB1436

CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-50μA ; I _E =0	-30			V
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-1mA ; I _B =0	-20			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-50μA ; I _C =0	-6			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-4A ; I _B =-0.1A			-1.0	V
I _{CBO}	Collector cut-off current	V _{CB} =-20V ; I _E =0			-0.5	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V ; I _C =0			-0.5	μA
h _{FE}	DC current gain	I _C =-0.5A ; V _{CE} =-2V	180		390	
f _T	Transition frequency	I _E =50mA ; V _{CE} =-6V ; f=30MHz		120		MHz
C _{ob}	Collector output capacitance	I _E =0 ; V _{CB} =-20V ; f=1MHz		60		pF

Silicon PNP Power Transistors

2SB1436

PACKAGE OUTLINE

